LT1007, LT1007A, LT1037, LT1037A LOW-NOISE, HIGH-SPEED, PRECISION OPERATIONAL AMPLIFIERS

SLOS017C - D3195, FEBRUARY 1989 - REVISED JANUARY 1993

16 NC

15 NC

13 V_{CC+}

11 NC

10 NC

9 NC

12 OUT

14 🛮 V_{IO} TRIM

DW PACKAGE (TOP VIEW)

NC

V_{IO} TRIM **1** 3

NC 1 2

IN – Π

NC [

5

7

IN+

V_{CC} – []

• Maximum Equivalent Input Noise Voltage:

3.8 nV/ $\sqrt{\text{Hz}}$ at 1 kHz 4.5 nV/ $\sqrt{\text{Hz}}$ at 10 Hz

- Low Peak-to-Peak Equivalent Input Noise Voltage: 60 nV Typ From 0.1 Hz to 10 Hz
- Slew Rate (LT1037 and LT1037A): 11 V/µs Min

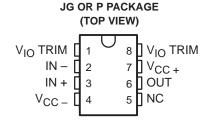
LT1007A and LT1037A Specifications:

• High Voltage Amplification: $7 \text{ V/}\mu\text{V Min, R}_L = 2 \text{ k}\Omega$ $3 \text{ V/}\mu\text{V Min, R}_L = 600 \Omega$

Low Input Offset Voltage:
 25 μV Max

 Low Input Offset Voltage Temperature Coefficient: 0.6 μV/°C Max

Common-Mode Rejection Ratio: 117 dB Min



NC - No internal connection

description

These monolithic operational amplifiers feature extremely low-noise performance and out

standing precision and speed specifications. The typical differential voltage amplification (at $T_A = 25^{\circ}C$) of these devices is an extremely high 20 V/ μ V driving a 2-k Ω load to ± 12 V and 12 V/ μ V driving, a 600- Ω load to ± 10 V.

In the design, processing, and testing of the device, particular attention has been paid to the optimization of the entire distribution of several key parameters. Consequently, the specifications of even the lowest-cost grades (the LT1007C and the LT1037C) have been greatly improved compared to equivalent grades of competing amplifiers.

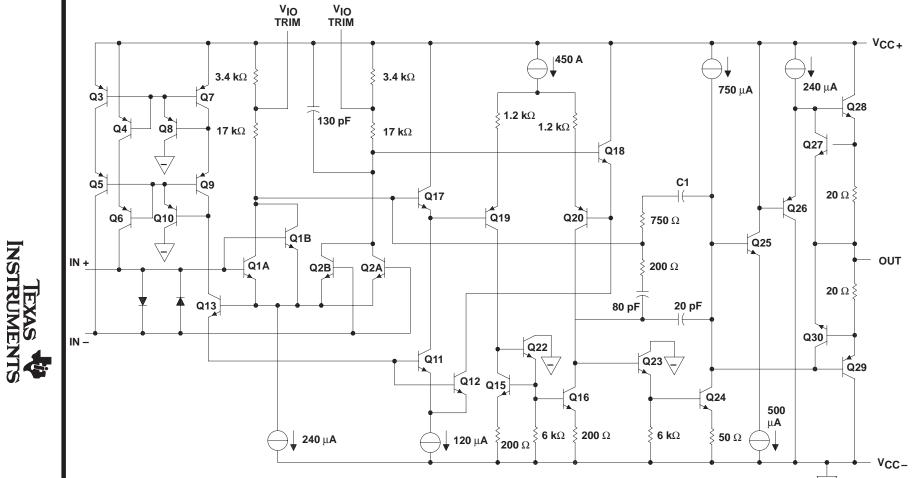
AVAILABLE OPTIONS

	V max	PACKAGE						
TA	V _{IO} max AT 25°C	SMALL-OUTLINE (DW)	CERAMIC DIP (JG)	PLASTIC DIP (P)				
	60 μV	LT1007CDW	_	LT1007CP				
0°C to	25 μV	_	_	LT1007ACP				
70°C	60 μV	LT1037CDW	_	LT1037CP				
	25 μV	_	_	LT1037ACP				
	60 μV	_	LT1007MJG	LT1007MP				
−55°C to	25 μV	_	LT1007AMJG	LT1007AMP				
125°C	60 μV	_	LT1037MJG	LT1037MP				
	25 μV	_	LT1037AMJG	LT1037AMP				

The DW packages are available taped and reeled. Add the suffix R to the device type, (e.g.,LT1007CDWR).

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schematic



C1 = 110 pF for LT1007 C1 = 12 pF for LT1037

All component values shown are nominal.

LT1007, LT1007A, LT1037, LT1037A LOW-NOISE, HIGH-SPEED, PRECISION OPERATIONAL AMPLIFIERS

SLOS017C - D3195, FEBRUARY 1989 - REVISED JANUARY 1993

absolute maximum ratings over operating free-air temperature range (unless otherwise noted)

Supply voltage, V _{CC+} (see Note 1)	22 V
Supply voltage, V _{CC}	–22 V
Input voltage	
Duration of output short circuit	
Differential input current (see Note 2)	±25 mA
Power dissipation	See Dissipation Rating Table
Operating free-air temperature range:	
LT1007C, LT1007AC, LT1037C, LT1037AC	0°C to 70°C
LT1007M, LT1007AM, LT1037M, LT1037AM	–55°C to 125°C
Storage temperature range	65°C to 150°C
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds: DW and P page 1.0 seconds: DW and P page 2.0 seconds: DW and P page	ckages 260°C
Lead temperature 1.6 mm (1/16 inch) from case for 60 seconds: JG package	

NOTES: 1. All voltage values, unless otherwise noted, are with respect to the midpoint between V_{CC+} and V_{CC-} .

2. The inputs are protected by back-to-back diodes. Current limiting resistors are not used in order to achieve low noise. Excessive input current will flow if a differential input voltage in excess of approximately ± 0.7 V is applied between the inputs, unless some limiting resistance is used.

DISSIPATION RATING TABLE

PACKAGE	$T_{\mbox{A}} \le 25^{\circ}\mbox{C}$ Power rating	DERATING FACTOR ABOVE T _A = 25° C	T _A = 70°C POWER RATING	T _A = 125° C POWER RATING
DW	1025 mW	8.2 mW/°C	656 mW	N/A
JG	1050 mW	8.4 mW/°C	672 mW	210 mW
Р	1000 mW	8 mW/°C	640 mW	200 mW

recommended operating conditions

			C-SUFFIX			M-SUFFIX			UNIT
			MIN	NOM	MAX	MIN	NOM	MAX	UNIT
Supply voltage, V _{CC+}			4	15	22	4	15	22	V
Supply voltage, V _{CC} _			-4	-15	-22	- 4	-15	-22	V
Input voltage V		T _A = 25 ° C	±11			±11			V
Input voltage, V _I		T _A = full range	±10.5			±10.3			٧
Operating free-air temperature, T _A		0		70	-55		125	°C	

LT1007, LT1007A, LT1037, LT1037A LOW-NOISE, HIGH-SPEED, PRECISION OPERATIONAL AMPLIFIERS

SLOS017C - D3195, FEBRUARY 1989 - REVISED JANUARY 1993

electrical characteristics, $V_{\mbox{\footnotesize CC}\pm}$ = $\pm 15~\mbox{\footnotesize V}$

	DADAMETED TEST CONDITIONS		т.	LT1007C, LT1037C			LT1007AC, LT1037AC			UNIT
	PARAMETER	TEST CONDITIONS	TA	MIN	TYP	MAX	MIN	TYP	MAX	UNII
V _{IO}	Input offset voltage	See Note 3	25 ° C		20	60		10	25	μV
V10	Input onset voltage	OCC NOIC S	0°C to 70°C			110			50	μν
αΝΙΟ	Average temperature coefficient of input offset voltage		0°C to 70°C			1			0.6	μV/°C
li o	Input offset surrent		25°C		12	50		7	30	nA
lio	Input offset current		0°C to 70°C			70			40	HA
lin.	Input bias current		25°C		±15	±55		±10	±35	nA
IB	input bias current		0°C to 70°C			±75			±45	IIA
	Dools output voltogo	$R_L = 2 k\Omega$	25°C	±12.5	±13.5		±13	±13.8		
VOМ	Peak output voltage swing	R _L = 600 Ω	25° C	±10.5	±12.5		±11	±12.5		V
	Swilig	$R_L = 2 k\Omega$	0°C to 70°C	±12			±12.5			
		$R_L \ge 2 k\Omega$, $V_O = \pm 12 V$	25° C	5	20		7	20		V/μV
	Large-signal	$R_L \ge 1 \Omega$, $V_O = \pm 10 V$	25° C	3.5	16		5	16		
AVD	differential voltage	$R_L \ge 600 \Omega$, $V_O = \pm 10 V$	25° C	2	12		3	12		
	amplification	$R_L \ge 2 \text{ k}\Omega, V_O = \pm 10 \text{ V}$	0°C to 70°C	2.5			4			
		$R_L \ge 1 \text{ k}\Omega, V_O = \pm 10 \text{ V}$	0°C to 70°C	2			2.5	-		
r _i (CM)	Common-mode input resistance		25°C		5			7		GΩ
r _O	Open-loop output resistance		25°C		70			70		Ω
CMRR	Common-mode	V _{IC} = ±11 V	25° C	110	126		117	130		dB
CIVIKK	rejection ratio	$V_{IC} = \pm 10.5 \text{ V}$	0°C to 70°C	106			114			uБ
kovr	Supply voltage	$V_{CC\pm} = \pm 4 \text{ V to } \pm 18 \text{ V}$	25°C	106	126		110	130		dB
ksvr	rejection ratio	$V_{CC\pm} = \pm 4.5 \text{ V to } \pm 18 \text{ V}$	0°C to 70°C	102			106			ub_
		LT1007C, LT1007AC	25°C		80	140		80	120	
P_{D}	Power dissipation	LT1037C, LT1037AC	25°C		85	140		80	130	mW
			0°C to 70°C			160			144	

NOTE 3: V_{IO} measurements are performed by automatic test equipment approximately 0.5 seconds after application of power.

LT1007, LT1007A, LT1037, LT1037A LOW-NOISE, HIGH-SPEED, PRECISION OPERATIONAL AMPLIFIERS

SLOS017C - D3195, FEBRUARY 1989 - REVISED JANUARY 1993

electrical characteristics, $V_{CC\pm}$ = $\pm 15~V$

			.T1007M, LT1037M		LT1007AM, LT1037AM			UNIT		
			, ,	MIN	TYP	MAX	MIN	TYP	MAX	
V	Innut offeet voltage	See Note 3	25°C		20	60		10	25	μV
VIO	Input offset voltage	See Note 3	−55°C to 125°C			160			60	μν
αVIO	Average temperature coefficient of input offset voltage		-55°C to 125°C			1			0.6	μV/°C
lio.	Input offset current		25°C		12	50		7	30	nA
lio	input onset current		−55°C to 125°C			85			50	IIA
I _{IB}	Input bias current		25°C		±15	±55		±10	±35	nA
אוי	Input bias current		−55°C to 125°C			±95			±60	11/4
	Peak output voltage	$R_L = 2 k\Omega$	25°C	±12.5	±13.5		±13	±13.8		V
VOM	swing	R _L = 600 Ω	25°C	±10.5	±12.5		±11	±12.5		
		$R_L = 2 k\Omega$	−55°C to 125°C	±12			±12.5			
	Large-signal differential voltage amplification	$R_L \ge 2 k\Omega$, $V_O = \pm 12 V$	25°C	5	20		7	20		V/μV
		$R_L \ge 1 \text{ k}\Omega, V_O = \pm 10 \text{ V}$	25°C	3.5	16		5	16		
AVD		$R_L \ge 600 \Omega$, $V_O = \pm 10 V$	25°C	2	12		3	12		
		$R_L \ge 2 \text{ k}\Omega, V_O = \pm 10 \text{ V}$	−55°C to 125°C	2			3			
		$R_L \ge 1 \text{ k}\Omega, V_O = \pm 10 \text{ V}$	−55°C to 125°C	1.5			2			
ri(CM)	Common-mode input resistance		25°C		5			7		GΩ
r _O	Open-loop output resistance		25°C		70			70		Ω
CMRR	Common-mode	$V_{IC} = \pm 11 \text{ V}$	25°C	110	126		117	130		40
CIVIKK	rejection ratio	V _{IC} = ±10.3 V	−55°C to 125°C	104			112			dB
le	Supply voltage	$V_{CC\pm} = \pm 4 \text{ V to } \pm 18 \text{ V}$	25°C	106	126		110	130		٩D
ksvr	rejection ratio	$V_{CC\pm} = \pm 4.5 \text{ V to } \pm 18 \text{ V}$	−55°C to 125°C	100			104			dB
		LT1007M, LT1007AM	25°C		80	140		80	120	
P_{D}	Power dissipation	LT1037M, LT1037AM	25°C		85	140		80	130	mW
			−55°C to 125°C			170		:	150	

NOTE 3: V_{IO} measurements are performed by automatic test equipment approximately 0.5 seconds after application of power.

LT1007, LT1007A, LT1037, LT1037A LOW-NOISE, HIGH-SPEED, PRECISION OPERATIONAL AMPLIFIERS

SLOS017C - D3195, FEBRUARY 1989 - REVISED JANUARY 1993

operating characteristics, $V_{CC\pm}$ = ± 15 V, T_A = $25\,^{\circ}C$

PARAMETER		TEST CONDITIONS	LT1007, LT1007A			LT1007, LT1007A			ш
		TEST CONDITIONS	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
SR	Claw rata	$R_L \ge 2 \text{ k}\Omega, A_{VD} \ge 1 \text{ (LT1007, LT1007A)}$	1.7	2.5		11	15		\//uo
SK	Slew rate	$R_L \ge 2 \text{ k}\Omega, A_{VD} \ge 5 \text{ (LT1037, LT1037A)}$	1.7	2.5		111			V/μs
V _{N(PP)}	Peak-to-peak equivalent input noise voltage	f = 0.1 Hz to 10 Hz, See Note 4		0.06	0.13		0.06	0.13	μV
.,	Equivalent input noise voltage	f = 10 Hz		2.8	4.5		2.8	4.5	nV/√Hz
Vn		f = 1 kHz		2.5	3.8		2.5	3.8	
	Equivalent input	f = 10 kHz, See Note 5		1.5	4		1.5	4	pA/√Hz
l'n	noise current	f = 1 kHz, See Note 5		0.4	0.6		0.4	0.6	p <i>e</i> /∀HZ
GBW	Gain handwidth product	f = 100 kHz	5	8					MHz
	Gain bandwidth product	f = 10 kHz, A _V ≥ 15				45	60		IVIIIZ

NOTES: 4. See the test circuit and frequency response curve for 0.1-Hz to 10-Hz noise (Figure 39) in the Applications Information section.

^{5.} See the test circuit for current noise measurement (Figure 40) in the Applications Information section.

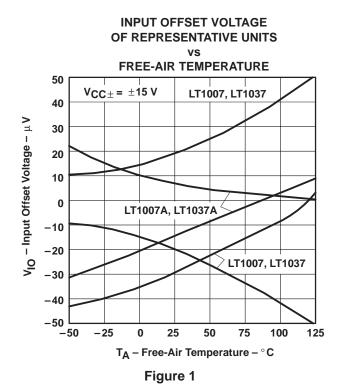
SLOS017C - D3195, FEBRUARY 1989 - REVISED JANUARY 1993

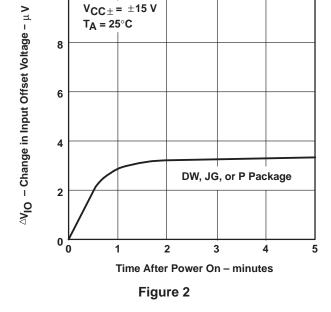
TYPICAL CHARACTERISTICS

table of graphs

			FIGURE
V _{IO}	Input offset voltage	vs Temperature	1
ΔV_{IO}	Change in input offset voltage	vs Time after power on vs Time (long-term stability)	2 3
lio	Input offset current	vs Temperature	4
I _{IB}	Input bias current	vs Temperature over common-mode range	5 6
	Common-mode limit voltage	vs Free-air temperature	7
VOM	Maximum peak output voltage swing	vs Load resistance vs Frequency	8 9
AVD	Differential voltage amplification	vs Frequency vs Frequency (LT1007) vs Frequency (LT1037) vs Temperature vs Load resistance vs Supply voltage at $2 \text{ k}\Omega$ and 600Ω	10 11 12 13 14 15
V _{ID}	Differential input voltage	vs Output voltage	16
CMRR	Common-mode rejection ratio	vs Frequency	17
ksvr	Supply voltage rejection ratio	vs Frequency	18
SR	Slew rate	vs Free-air temperature (LT1007) vs Free-air temperature (LT1037)	19 20
ф	Phase shift	vs Frequency (LT1007) vs Frequency (LT1037)	11 12
φm	Phase margin	vs Free-air temperature (LT1007) vs Free-air temperature (LT1037)	19 20
V _n	Equivalent input noise voltage	vs Free-air temperature vs Time (0.01-Hz to 1-Hz noise) vs Frequency vs Bandwidth vs Supply voltage	21 22 23 24 25
In	Equivalent input noise current Total noise	vs Frequency vs Source resistance	26 27
GBW	Gain bandwidth product	vs Free-air Temperature (LT1007) vs Free-air Temperature (LT1037)	19 20
los	Short-circuit output current	vs Time (from short to GND)	28
lcc	Supply current	vs Supply voltage	29
z _O	Closed-loop output impedance	vs Frequency	30
	Pulse response (LT1037)	Small-signal (C _L = 15 pF) Large-signal	31 32
	Pulse response (LT1007)	Small-signal (C _L = 15 pF) Large-signal	33 34

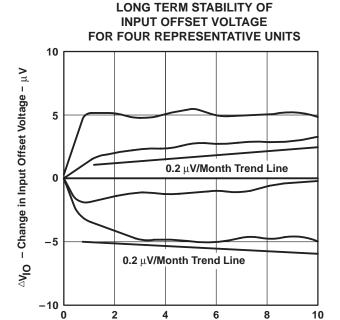
10





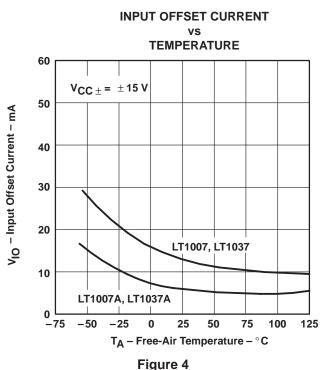
INPUT OFFSET VOLTAGE

TIME AFTER POWER ON



t - Time - months

Figure 3



[†] Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.



20

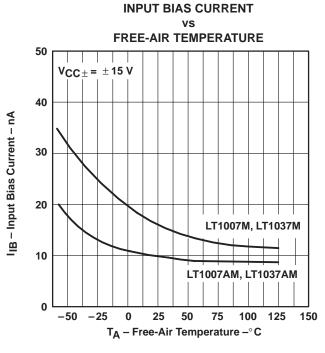
<u>-</u>15

-10

INPUT BIAS CURRENT

COMMON-MODE INPUT VOLTAGE

TYPICAL CHARACTERISTICS[†]



15 **Device With Positive Input Current** IB - Input Bias Current - nA 10 5 $r_{i(CM)} = \frac{20 \text{ V}}{3 \text{ nA}} = 7 \text{ G}\Omega$ 0 -5 -10 **Device With Negative** Input Current -15 V_{CC±} = ±15 V T_A = 25°C -20

Figure 5

Figure 6

0

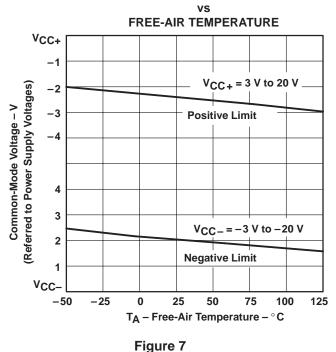
5

10

15

-5

COMMON-MODE INPUT VOLTAGE RANGE LIMITS



PEAK OUTPUT VOLTAGE SWING

V_{IC} - Common-Mode Input Voltage

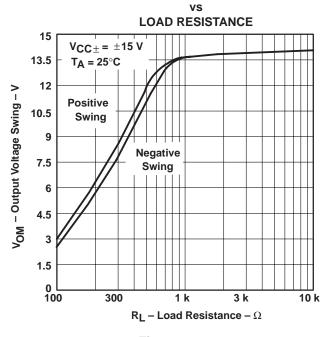


Figure 8

[†] Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS

PEAK-TO-PEAK OUTPUT VOLTAGE SWING

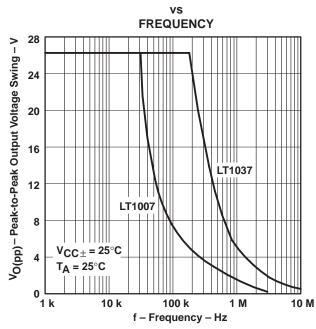


Figure 9

LT1007 DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

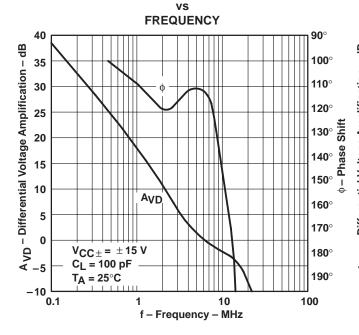


Figure 11

DIFFERENTIAL VOLTAGE AMPLIFICATION

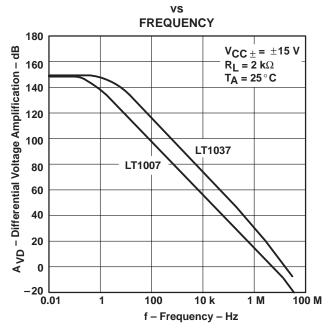


Figure 10

LT1037 DIFFERENTIAL VOLTAGE AMPLIFICATION AND PHASE SHIFT

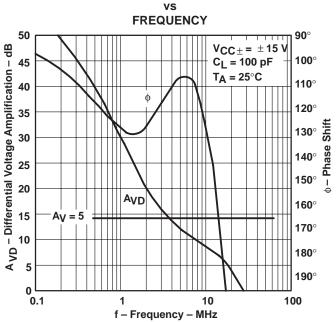


Figure 12

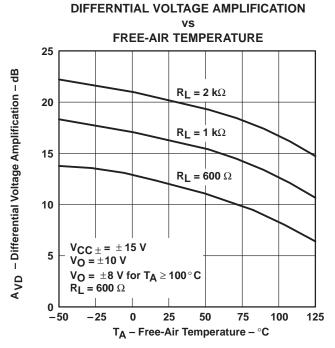
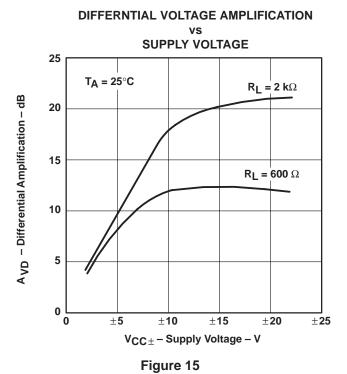


Figure 13



DIFFERNTIAL VOLTAGE AMPLIFICATION

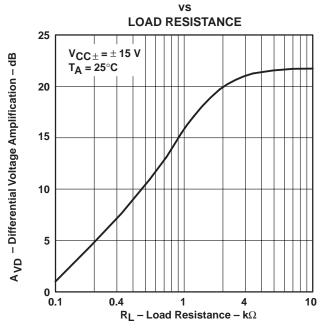


Figure 14

DIFFERNTIAL INPUT VOLTAGE

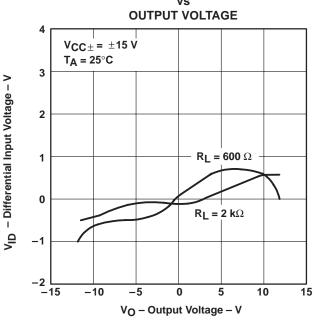


Figure 16

[†] Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.



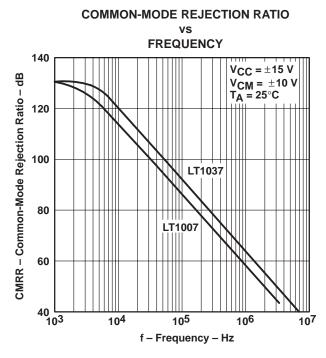


Figure 17

LT1007

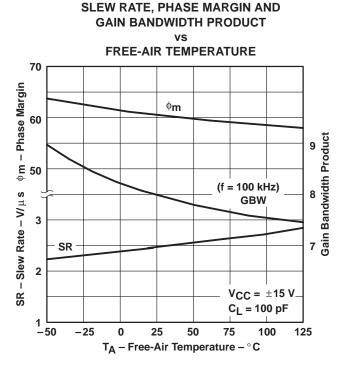


Figure 19

SUPPLY VOLTAGE REJECTION RATIO

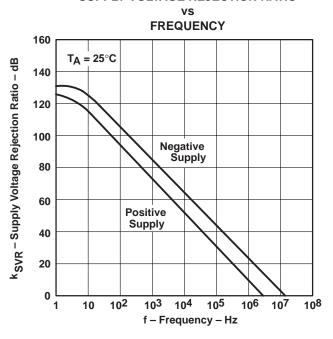


Figure 18

LT1037 SLEW RATE, PHASE MARGIN AND GAIN BANDWIDTH PRODUCT VS

FREE-AIR TEMPERATURE

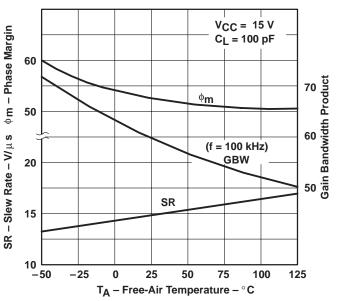


Figure 20

[†] Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.



TYPICAL CHARACTERISTICS†

EQUIVALENT INPUT NOISE VOLTAGE

FREE-AIR TEMPERATURE

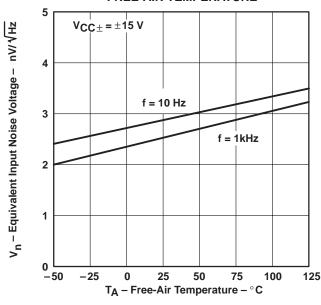


Figure 21

EQUIVALENT INPUT NOISE VOLTAGE OVER A 100-SECOND TIME PERIOD

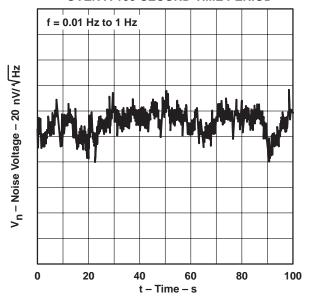


Figure 22

EQUIVALENT INPUT NOISE VOLTAGE

vs

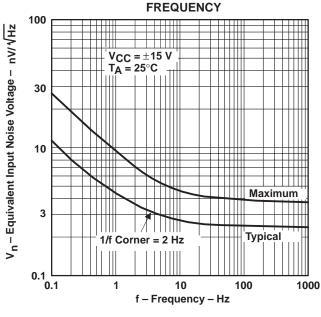


Figure 23

BROADBAND NOISE VOLTAGE 0.1 Hz TO INDICATED FREQUENCY

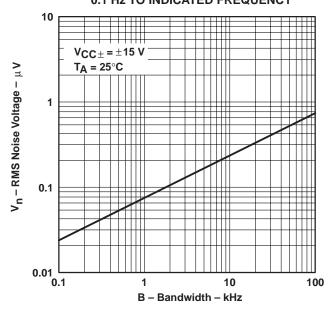


Figure 24

[†] Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.



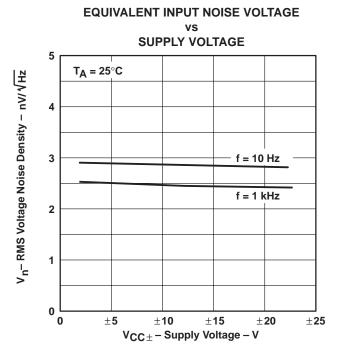
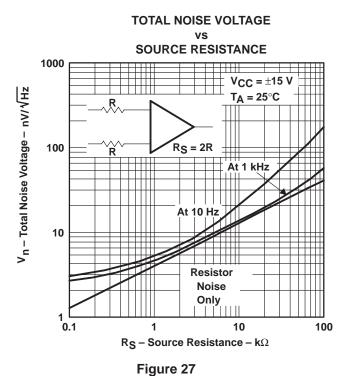


Figure 25



EQUIVALENT INPUT NOISE CURRENT

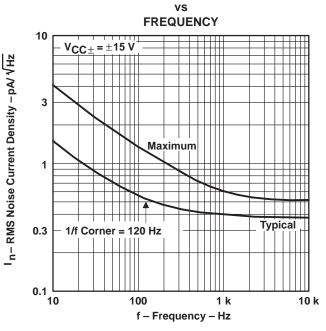


Figure 26

SHORT-CIRCUIT OUTPUT CURRENT

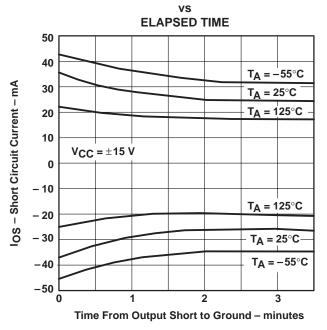


Figure 28

[†] Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.



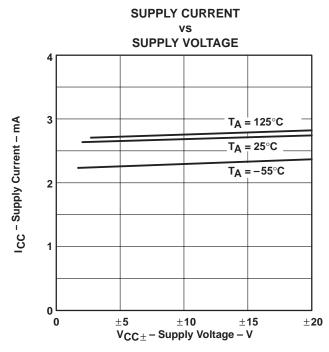


Figure 29

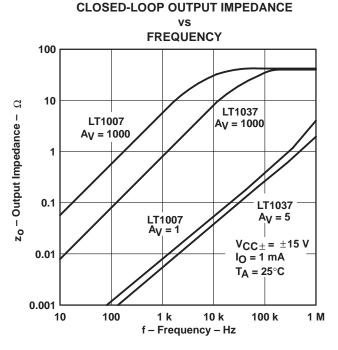


Figure 30

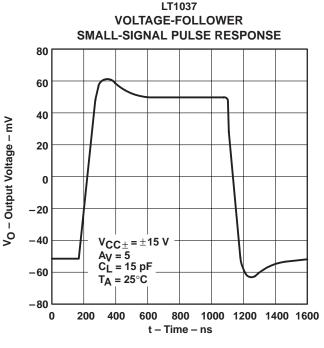
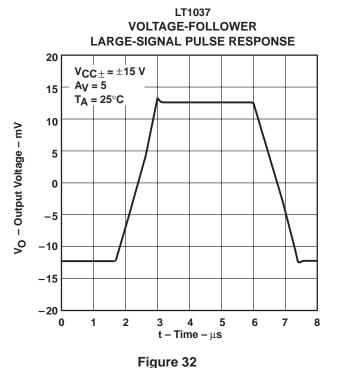


Figure 31

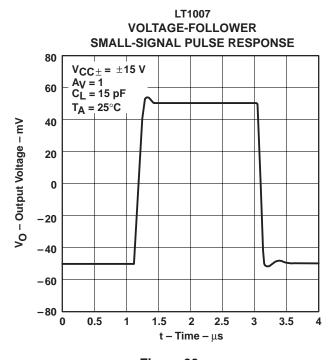


† Data at high and low temperatures are applicable within the rated operating free-air temperature ranges of the various devices.



SLOS017C - D3195, FEBRUARY 1989 - REVISED JANUARY 1993

TYPICAL CHARACTERISTICS



VOLTAGE-FOLLOWER LARGE-SIGNAL PULSE RESPONSE 8 $V_{CC\pm} = \pm 15 V$ $A_V = -1$ 6 T_A = 25°C Vo - Output Voltage - mV 4 2 0 -2 -4 -6 -8 2 6 8 10 12 14 16 $t - Time - \mu s$

I T1007

Figure 33

Figure 34

APPLICATION INFORMATION

general

The LT1007- and LT1037-series devices may be inserted directly into OP-07, OP-27, OP-37, and 5534 sockets with or without removal of external-compensation or nulling components. In addition, the LT1007 and LT1037 may be fitted to μ A741 sockets by removing or modifying external nulling components.

offset voltage adjustment

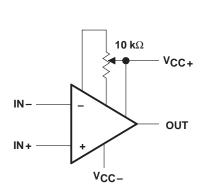
The input offset voltage and its change with temperature of the LT1007 and LT1037 are permanently trimmed to a low level at wafer testing . However, if further adjustment of V_{IO} is necessary, the use of a 10-k Ω nulling potentiometer, as shown in Figure 35, will not degrade drift with temperature. Trimming to a value other than zero creates a drift of $V_{IO}/300~\mu\text{V/°C}$ (e.g., if V_{IO} is adjusted to 300 μV , the change in temperature coefficient will be 1 $\mu\text{V/°C}$).

The adjustment range with a 10-k Ω potentiometer is approximately ± 2.5 mV. If a smaller adjustment range is needed, the sensitivity and resolution of the nulling can be improved by using a smaller potentiometer in conjunction with fixed resistors. The example in Figure 36 has an approximate null range of $\pm 200~\mu V$.

offset voltage and drift

Unless proper care is exercised, thermocouple effects at the contacts to the input terminals, caused by temperature gradients across dissimilar metals, can exceed the inherent temperature coefficient of the amplifier. Air currents should be minimized, package leads should be short, input leads should be close together, and input leads should be at the same temperature.





1 $k\Omega$ VCC+ **4.7 k**Ω 4.7 $k\Omega$ IN OUT IN₄ VCC-

Figure 35. Standard Adjustment

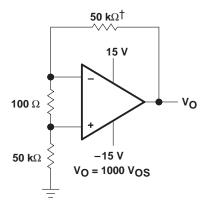
Figure 36. Improved Sensitivity Adjustment

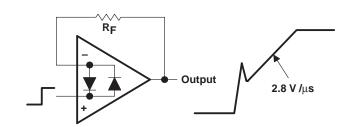
The circuit shown in Figure 37 can be used to measure offset voltage. In addition, with the supply voltages increased to ±20 V, it can be used as the burn-in configuration for the LT1007 and LT1037.

When $R_F \le 100 \Omega$ and the input is driven with a fast large-signal pulse (> 1 V), the output waveform will be as shown in Figure 38.

During the fast-feedthrough-like portion of the output, the input protection diodes effectively short the output to the input and a current, limited only by the output short-circuit protection, is drawn by the signal generator. When R_F is \geq 500 Ω , the output is capable of handling the current requirements ($I_1 \leq$ 20 mA at 10 V), the amplifier stays in its active mode, and a smooth transition occurs.

When R_F is > 2 k Ω , a pole will be created with R_F and the amplifier's input capacitance, creating additional phase shift and reducing the phase margin. A small capacitor (20 pF to 50 pF) in parallel with R_F will eliminate this problem.





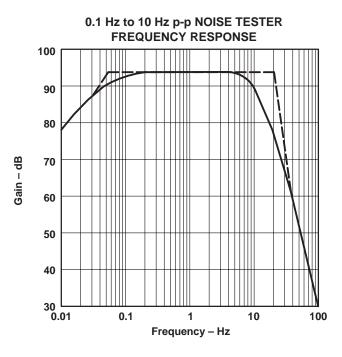
† Resistors must have low thermoelectric potential

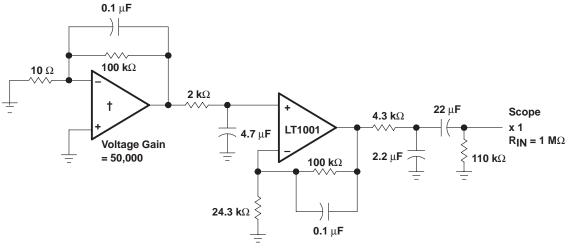
Figure 37. Test Circuit for Offset Voltage and Offset Voltage Drift With **Temperature**

Figure 38. Pulse Operation

noise testing

Figure 39 shows a test circuit for 0.1-Hz to 10-Hz peak-to-peak noise measurement of the LT1007 and LT1037. The frequency response of this noise tester indicates that eeethe 0.1 Hz corner is defined by only one zero. Because the time limit acts as an additional zero to eliminate noise contributions from the frequency band below 0.1 Hz, the test time to measure 0.1-Hz to 10-Hz noise should not exceed 10 seconds.





† Device under test

NOTE: All capacitor values are for non-polarized capacitors only.

Figure 39. 0.1-Hz To 10-Hz Noise Test Circuit



Special test precautions are required to measure the typical 60-nV peak-to-peak noise performance of the LT1007 and LT1037:

- 1. The device should be warmed up for at least five minutes. As the operational amplifier warms up, the offset voltage typically changes 3 μ V, due to the chip temperature increasing 10°C to 20°C from the moment the power supplies are turned on. In the 10-second measurement interval, these temperature-induced effects can easily exceed tens of nanovolts.
- 2. The device must be well shielded from air currents to eliminate thermoelectric effects. In excess of a few nanovolts, thermoelectric effects would invalidate the measurements.
- 3. Sudden motion in the vicinity of the device can produce a feedthrough effect that increases observed noise.

When measuring noise on a large number of units, a noise-voltage density test is recommended. A 10-Hz noise-voltage density measurement will correlate well with a 0.1-Hz to 10-Hz peak-to-peak noise reading since both results are determined by the white noise and the location of the 1/f corner frequency.

Figure 40 shows a circuit that measures noise current and presents the formula for calculating noise current.

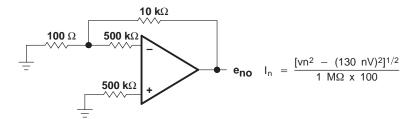


Figure 40. Noise Test Circuit

The LT1007 and LT1037 achieve low noise, in part, by operating the input stage at 120 μ A versus the typical 10 μ A for most other operational amplifiers. Voltage noise is directly proportional to the square root of the stage current; therefore, the LT1007 and LT1037 noise current is relatively high. At low frequencies, the low 1/f current-noise corner frequency (\approx 120 Hz) minimizes noise current to some extent.

In most practical applications, however, noise current will not limit system performance; this is illustrated in Figure 27, where:

total noise = $[(noise voltage)^2(noise current x R_S)^2 + (resistor noise)^2]^{1/2}$

Three regions can be identified as a function of source resistance:

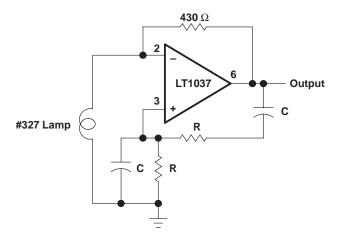
(i) $R_S \le 400 \Omega$ Voltage noise dominates in region (i)

(ii) $R_S = 400~\Omega$ to 50 k Ω at 1 kHz Resistor noise dominates in region (ii) $R_S = 400~\Omega$ to 8 k Ω at 10 kHz

(iii) R_S > 50 Ω at 1 kHz Current noise dominates in region (iii) R_S > 8 k Ω at 10 Hz

The LT1007 and LT1037 should not be used in region (iii) where total system noise is at least six times higher than the noise voltage of the operational amplifier (i.e., the low-voltage noise specification is completely wasted).

The sine wave generator application shown below, utilizes the low-noise and low-distortion characteristics of the LT1037.



$$\begin{split} f &= \frac{1}{2\pi \ RC} \\ R = &1591.5\Omega \pm 0.1 \ \% \\ C = &0.1 \ \mu F \pm 0.1 \ \% \end{split}$$

TOTAL HARMONIC DISTORTION $\leq 0.0025\%$ NOISE $\leq 0.001\%$

AMPLITUDE = ± 8 V OUTPUT FREQUENCY = 1.000 kHz FOR VALUES GIVEN $\pm 0.4\%$

Figure 41. Ultra-Pure 1-kHz Sine-Wave Generator

EQUIVALENT INPUT NOISE VOLTAGE OVER A 10-SECOND PERIOD

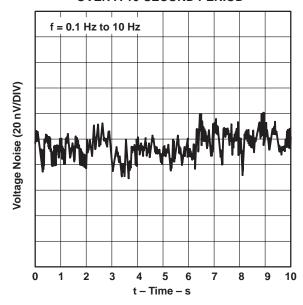
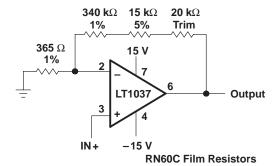


Figure 42



The high gain and wide bandwidth of the LT1037 and (LT1007) is useful in low-frequency high-closed-loop-gain amplifier applications. A typical precision operational amplifier may have an open loop gain of one million with 500 kHz bandwidth. As the gain error plot shows, this device is capable of 0.1% amplifying accuracy up to 0.3 Hz only. Even instrumentation range signals can vary at a faster rate. The LT1037's gain precision – bandwidth product is 200 times higher, as shown.

Figure 43. Gain 1000 Amplifier With 0.01% Accuracy, DC to 5 Hz



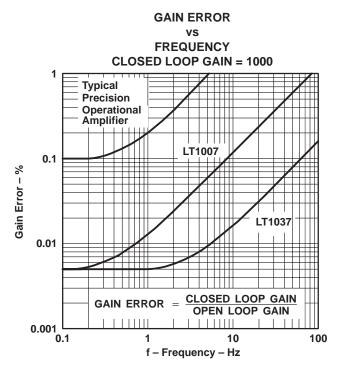
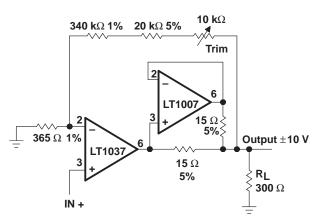
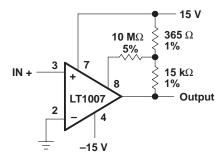


Figure 44.



The addition of the LT1007 doubles the amplifier's output drive to $\pm 33\,$ mA. Gain accuracy is 0.02%, slightly degraded compared to above because of self heating of the LT1037 under load.

Figure 46. Precision Amplifier Drives 300- Ω Load to \pm 10 V



Positive feedback to one of the nulling terminals creates approximately 5 μV of hysteresis. Output can sink 16 mA.

Input offset voltage is typically changed less than 5 μV due to the feedback.

Figure 45. Microvolt Comparator With Hysteresis

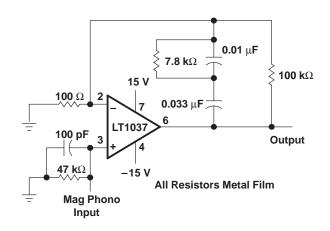


Figure 47. Phono Preamplifier

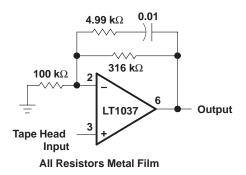


Figure 48. Tape Head Amplifier

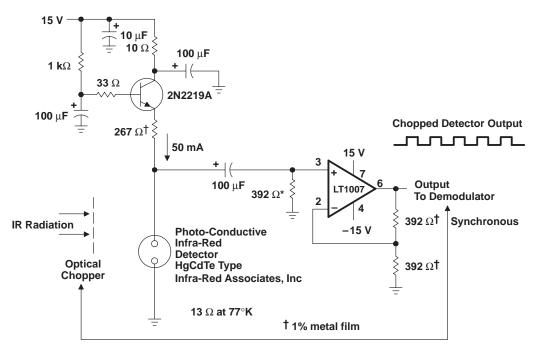


Figure 49. Infra-Red Detector Preamplifier

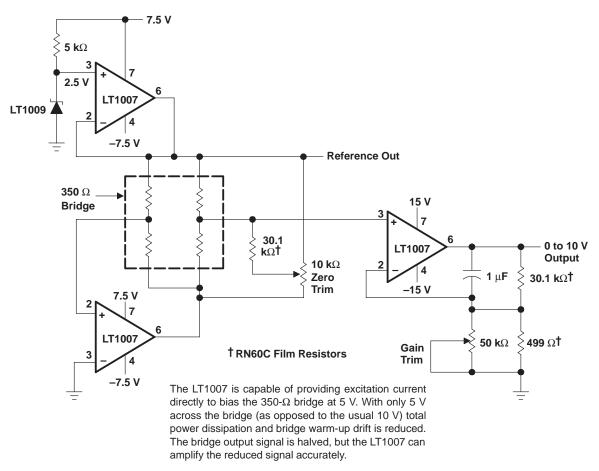


Figure 50. Strain Gauge Signal Conditioner With Bridge Excitation

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